

Table of Contents

Preface

Charge Collection Scanning Microscopy: Non-Conventional Applications	1
A. Castaldini and A. Cavallini	
EBIC Study of Field Effect Transistors on Modulation-Doped AlGaAs/InGaAs/GaAs Heterostructures	13
B. Sieber and J.-. Farvacque	
EBIC of Strained Si/SiGe 2DEGs Showing Lateral Electron Confinement	25
C.E. Norman, N. Griffin, D.D. Arnone, D.J. Paul, M. Pepper, B. Gallas and J.M. Fernández	
Laser Induced Mapping for Separation of Bulk and Surface Recombination	33
H.-. Ostendorf and A.L. Endrös	
Analysis of Minority Carrier Diffusion in the Presence of a Dislocation Array: Effective Diffusion Length, Luminescence Efficiency and Dark Current	45
C. Donolato	
Detection and Characterisation of 'Sleeping' Defects in Silicon by LBIC Scan Maps at 80 K.	53
S. Martinuzzi, I. Périchaud and S.A. McHugo	
Combined MOS/EBIC and Tem Study of Electrically Active Defects in SOI Wafers	61
O.V. Kononchuk, I.E. Bondarenko and G.A. Rozgonyi	
Characterization of Laser Structures by EBIC Measurements and Simulation	69
I. Rechenberg, H. Wenzel, A. Knauer and G. Beister	
Evaluation of p-n Junction Position and Channel Length in Si Devices with Resolution of a Few Nanometers by Low-Energy EBIC	77
M. Kittler and J. Lärz	
Monte Carlo Simulation of the Recombination Contrast of Dislocations	89
N. Tabet	
EBIC Characterization of Oxygen Precipitation and Denuded Zone in Intrinsically Gettered P-Type Czochralski Silicon	97
S. Spiga, A. Castaldini, A. Cavallini, M.L. Polignano and F. Cazzaniga	
Impact of Phosphorus Diffusion on the Contamination Level of Dislocations in Deformed Float Zone Silicon as Studied by Beam Injection Techniques	105
K. Knobloch, M. Kittler, W. Seifert, J.J. Simon and I. Périchaud	
LBIC Investigations of the Lifetime Degradation by Extended Defects in Multicrystalline Solar Silicon	115
M. Rinio, H.J. Möller and M. Werner	
Determination of the Surface Recombination Velocity and of Its Evolution in Monocrystalline Silicon by the Light Beam Induced Current Technique in Planar Configuration	123
S. Spadoni, M. Acciarri, G. Barbi and S. Pizzini	
SEM-EBIC Study of Defects in Epitaxial AlGaN Layers	131
G.N. Panin, O.V. Kononenko, V.N. Matveev, E.B. Yakimov and O. Ambacher	
Minority Carrier Diffusion Length in AlGaN: A Combined Electron Beam Induced Current and Transmission Microscopy Study	139
A. Cremades, M. Albrecht, A. Voigt, J. Krinke, R. Dimitrov, O. Ambacher and M. Stutzmann	
Ion Beam Induced Luminescence	147
K.G. Malmqvist	
Nanocharacterization of Semiconductors by Scanning Photoluminescence Microscopy	151
P. Fischer, J. Christen, M. Zacharias, H. Nakashima and K. Hiramatsu	
Cathodoluminescence Microscopy of Semiconductor Devices Using a Novel Detector with High Collection and Backscattered Electron Rejection Efficiency	159
J.C.H. Phang, D.S.H. Chan, W.K. Chim, Y.Y. Liu and X. Liu	
Cathodoluminescence Study on ZnO and GaN	171
T. Sekiguchi, N. Ohashi and H. Yamane	
Cathodoluminescence Investigation of Diffusion Studies on the Arsenic Sublattice in Gallium Arsenide	183
R.F. Scholz, U.M. Gösele, O. Breitenstein, U. Egger and T.Y. Tan	

Cathodoluminescence from Nanocrystalline Silicon Films in the Scanning Electron Microscope	
B. Méndez, J. Piqueras, R. Plugaru, G. Craciun, N. Nastase, A. Cremades and E. Nogales	191
The Spatial Distribution of Modulated CL Signal in Inhomogeneous Semiconductors with Large Diffusion Length	
V.A. Kireev, I.I. Razgonov and E.B. Yakimov	199
Effect of Plastic Deformation on the Luminescence of ZnSe Crystals	
P. Fernández, J. Piqueras, A. Urbieto, Y.T. Rebane and Y. Shreter	207
Effect of Erbium on the Luminescence Properties of GaSb Crystals	
P. Hidalgo, B. Méndez, J. Piqueras, J. Plaza and E. Diéguez	215
Direct Imaging of the Crystalline and Chemical Nanostructure of Ga,IN-Nitrides by Highly Spatially-, Spectrally- and Time-Resolved Cathodoluminescence	
D. Rudloff, F. Bertram, T. Riemann, J. Christen, T. Böttcher, H. Selke, D. Hommel and K. Hiramatsu	221
Cathodoluminescence and Photoluminescence Characterisation of Etched Mesas of ZnTe/ZnMgTe Quantum Wells under Tensile Strain	
S. Dassonneville, Y.-. Niquet, B. Sieber and H. Mariette	229
Cathodoluminescence Study of Defect Distribution at Different Depths in Films SiO₂/Si	
M.V. Zamoryanskaya, V.I. Sokolov, A.A. Sitnikova and S.G. Konnikov	237
Cathodoluminescence Dependence on Beam Generation Conditions and Surface Properties of Materials	
S. Achour, M.T. Belahrache, A. Harabi and N. Tabet	243
Neat Field Optics: Comeback of Light in Microscopy	
D.W. Pohl	251
Near-Field Cathodoluminescence (NF-CL) Investigations on Semiconducting Materials	
V. Ebinghaus, R.M. Cramer, R. Heiderhoff and L.J. Balk	257
Local Stress, Surface Reconstruction, and Bulk Defect Nucleation: An STM Study on Silicon	
H.J. Müssig and J. Dąbrowski	261
Correlative SEM/STM Study of Local Electronic Properties in Compound Semiconductors	
J. Piqueras, G.N. Panin, C. Díaz-Guerra, P. Hidalgo and B. Méndez	273
Observation and Modelization of the Electrostatic Force due to the Local Variations of the Surface Potential by Electrostatic Force Microscopy (EFM)	
J.F. Bresse	283
The Sloc Positron Beam Technique – A Unique Tool for the Study of Vacancy-Type Defects in Semiconductors	
R. Krause-Rehberg, S. Eichler, J. Gebauer and F. Börner	291
Minority Carrier Transient Spectroscopy of Copper-Silicide and Nickel-Disilicide Precipitates in Silicon	
O.F. Vyvenko	301
Grain Growth of ZnSe Recrystallized in the Solid Phase	
S. Fusil, A. Zozime, R. Pénelle, F. Grillon, C. Le Paven, A. Rivière and R. Triboulet	311
Lateral Doping Inhomogeneities as Revealed by μ-NEXAFS and μ-PES	
R.P. Mikalo, P. Hoffmann, T. Heller and D. Schmeißer	317
Application of Surface Electron Beam Induced Voltage Method for the Contactless Characterization of Semiconductor Structures	
E.I. Rau, A.N. Zhukov and E.B. Yakimov	327
Modification of Electronical and Optical Properties in SiO₂ Films by Electron Beam Irradiation	
H.J. Fitting, A. von Czarnowski, A.N. Trukhin, M. Goldberg and T. Barfels	333
Fabrication and Ellipsometric Investigation of Thin Films of Rare-Earth Oxides	
O.V. Fursenko, T.V. Semikina and A.N. Shmyrjeva	341
Non-Destructive Investigations of Co and CoSi_{2-x} Films on Si Substrate	
N.L. Dmitruk, O.V. Fursenko, A. Medvid, D. Knight and A. Grigonis	347
Characterization of Laser-Irradiated Cd_xHg_{1-x}Te Solid Solutions by Scanning Microscopy Method	
V.A. Gnatyuk	353

Scanning Acoustic Microscopes for the Investigation of Ferroelectric Properties of Materials	
X.G. Liu, L.J. Balk, G. Shafirstein, A. Eckau and Q.R. Yin	361
The Nature of the Electronic States of Cu₃Si-Precipitates in Silicon	
A. Sattler, H. Hedemann, A.A. Istratov, M. Seibt and W. Schröter	369
TEM and Photoluminescence Investigations of InGaAs/GaAs Quantum Well Layers	
C. Frigeri, A. Brinciotti, D.M. Ritchie and A. Di Paola	375
The Assessment of Micro-Analytical Techniques to the Semiconductor Manufacturing Environment	
J.L. Corbacho, A. Urquía, A. Fernández, G. Sánchez, M. Recio, V. Martín, F. Barbado, C. Morilla, A. Riloba and J.M. de la Hoz	383
Gate Oxide Defect Analysis Using Scanning Electron Microscopy (SEM)/Metal Oxide Semiconductor (MOS)/Electron Beam Induced Current (EBIC) with Sub-Nano Ampere Current Breakdown	
M. Tamatsuka and K. Miki	395
Defect Characterization in Metal-Oxide-Semiconductor Field-Effect-Transistors with Trench Gates by Electron Beam-Induced Current Technique	
H. Tomokage, Y. Ishiwata, H. Souno, M. Kawakami and N. Sonoda	407
Analysis of Non-Uniform Contamination Profiles by Lifetime Data	
M.L. Polignano, D. Caputo, G. Pavia and F. Zanderigo	413
Scanning Photoluminescence for Wafer Characterization	
V. Higgs, F. Chin and X.C. Wang	421
Failure Mode Analysis of a 0.25 μm CMOS Technology by Scanning Electron and Ion Beams	
D. Krüger, R. Rosenkranz, B. Tippelt, M. Kuhnert, K. Grießbach, A. Lamprecht and S. Hennecke	433
Failure Analysis of Neutron-Irradiated MQW InGaAsP/InP Lasers by EBIC	
M. Romero, D. Araújo, K. Gill, F. Vasey and R. García	443
Inline Analysis of Defects in Microelectronic Fabrication by Optical and Scanning Electron Microscopical Techniques	
C. Morilla and M. Kittler	457
Application of Small Pulsed Ion Beams for Depth Profiling on Beveled Semiconductor Structures	
D. Krüger, K. Iltgen and R. Kurps	465
Correlation of Cathodoluminescence and EBIC Contrast in GaAs/Al_xGa_{1-x}As Quantum Well Structures	
U. Jahn, R. Hey, H. Kostial and H.T. Grahn	473
EBIC and Cathodoluminescence Study of the Bonded Silicon Wafers	
K. Ikeda, T. Sekiguchi, S. Ito and M. Suezawa	481
Spatially Resolved Cathodoluminescence Study on CVD Homoepitaxial Diamond Film	
H. Watanabe, D. Takeuchi, H. Okushi, K. Kajimura and T. Sekiguchi	489
Cathodoluminescence Study of Heavily Proton Irradiated Heteroepitaxial n⁺-p InP/Si Solar Cells	
M. Romero, R.J. Walters, D. Araújo and R. García	497
Electrical Properties of SiGe Epitaxial Layers for Photovoltaic Application as Studied by Scanning Electron Microscopical Methods	
O. Krüger, W. Seifert, M. Kittler, A. Gutjahr, M. Konuma, K. Said and J. Poortmans	509
Stress Measurements in sub-μm Si Structures Using Raman Spectroscopy	
K.F. Dombrowski and I. De Wolf	519
Two Dimensional Mapping of pn Junctions by Electron Holography	
W.D. Rau, P. Schwander and A. Ourmazd	525
The Future of Beam Injection Techniques: Summary of the Round-Table Discussion Held at BIADS 98	
A. Endrös, A. Jakubowicz and Z.J. Radzimski	529